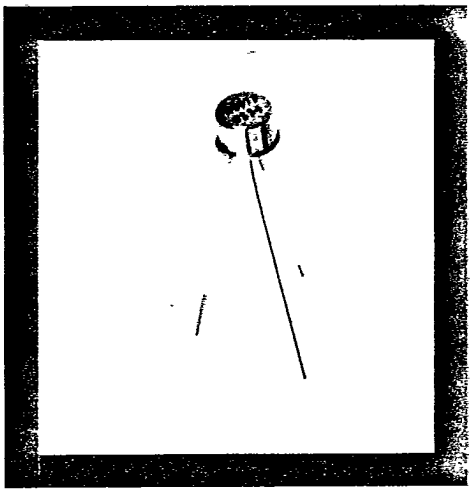
HUTSON INDUSTRIES

TRIAC's

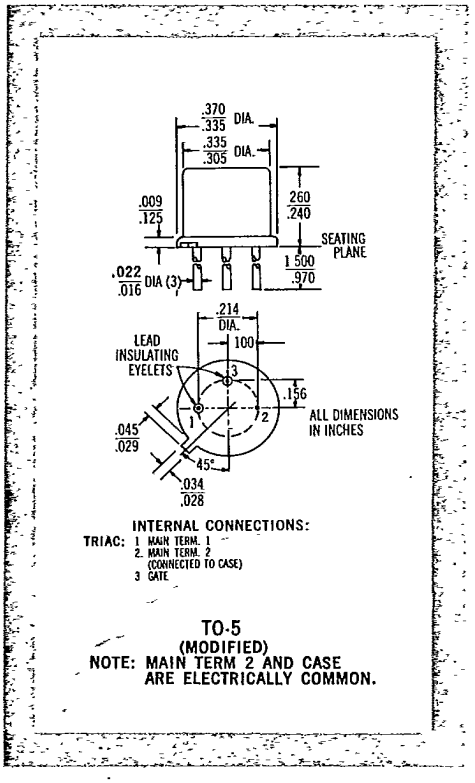
6 AMPERE TO-5 TRIAC



Advanced engineering and manufacturing technology at Hutson have produced highly reliable yet economical triacs for switching-device applications. Hutson triacs feature proprietary techniques that have proven advantages, which include an extremely dense, sodium-free proprietary glass to insure a positive hermetic seal, while eliminating the "punch-through" and "burn-through" associated with organic passivation materials.

Hutson triacs are bi-directional triode thyristors and may be switched from off-state to conduction for either polarity of applied voltage with positive or negative gate-trigger current. They are designed for control applications in lighting, heating, cooling and static switchng relays.

In addition to standard package configurations, all Hutson triacs are also available in chip form. Please consult Hutson Industries for additional information.



TO-5
(MODIFIED)
NOTE: MAIN TERM 2 AND CASE ARE ELECTRICALLY COMMON.

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PRELIMINARY DATA

HT--00006-1X

HUTSON INDUSTRIES

6 Ampere TO-5 TRIAC

		SYMBOL	V_{DROM}	DEVICE NO.	UNIT
MAXIMUM RATINGS	Repetitive Peak Off-State Voltage, Gate Open, and T_J = 100°C	V_{DROM}	50 100 200 300 400 500 600	HT06 HT16 HT26 HT36 HT46 HT56 HT66	VOLT
	RMS On-State Current at T_C = 75°C and Conduction Angle of 360°	$I_{T(RMS)}$		6	AMP
	Peak Surge (Non-Repetitive) On-State Current, One-Cycle, at 50Hz or 60Hz	I_{TSM}		80	AMP
	Peak Gate-Trigger Current for 3μsec, Max.	I_{GTM}		1	AMP
	Peak Gate-Power Dissipation at $I_{GT} \leq I_{GTM}$ for 3μsec. Max.	P_{GM}		20	WATT
	Average Gate-Power Dissipation	$P_{G(AV)}$		.2	WATT
	Storage Temperature Range	T_{stg}		−40 to +150	°C
	Operating Temperature Range, T_C	T_{oper}		−40 to +100	°C
ELECTRICAL CHARACTERISTICS At Maximum Ratings and Specified Case Temperatures	Peak Off-State Current, Gate Open,[2] T_J = 100°C V_{DROM} = Max. Rating	I_{DROM}		2 Max.	mA
	Maximum On-State Voltage at T_C = 25°C and i_T = 10 Amp (Peak)	V_{TM}		2.2 Max.	VOLT
	DC Holding Current, Gate Open and T_C = 25°C	I_{HO}		50 Max.	mA
	Critical Rate-of-Rise of Off-State Voltage[3] for V_D = V_{DROM}, Gate Open, T_C = 100°C	Critical dv/dt		5 Typ.	V/μsec.
	DC Gate-Trigger Current for V_D = 6VDC, R_L = 39Ω and at T_C = 25°C (T_2+Gate+, T_2−Gate−) Quads I and III (T_2+Gate−, T_2−Gate+) Quads II and IV (Note 1)	I_{GT}		50 Max. 80 Max.	mA
	DC Gate-Trigger Voltage for V_D = 6VDC, R_L = 39Ω and at T_C = 25°C	V_{GT}		2.5 Typ.	VOLT
	Gate-Controlled Turn-on Time for V_D = V_{DROM}, I_{GT} = 80mA, t_r = 0.1μsec., I_T = 10A (Peak) and T_C = 25°C	t_{gt}		2.5 Typ.	μsec.
	Thermal Resistance, Junction-to-Case	θ_{J-C}		3 Typ.	°C/W

PRELIMINARY DATA

PRINTED IN USA

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HT--- 00006-2X